

Organic Cocrystal based on Phthalocyanine with Ideal Packing Mode towards High-Performance Ambipolar Property

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Supplemental Figures

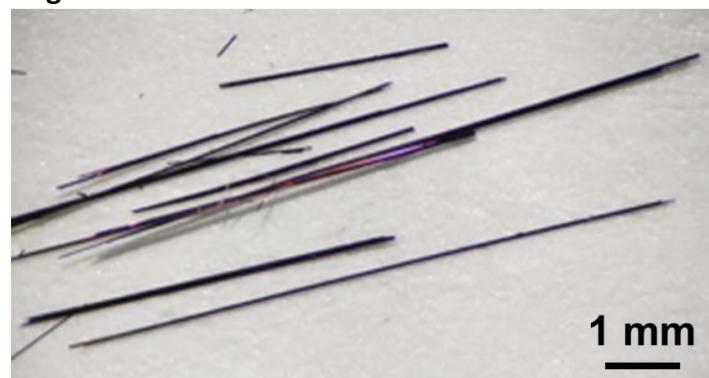


Fig. S1 Large crystal photo of ZnPc–F₁₆CuPc cocrystal.

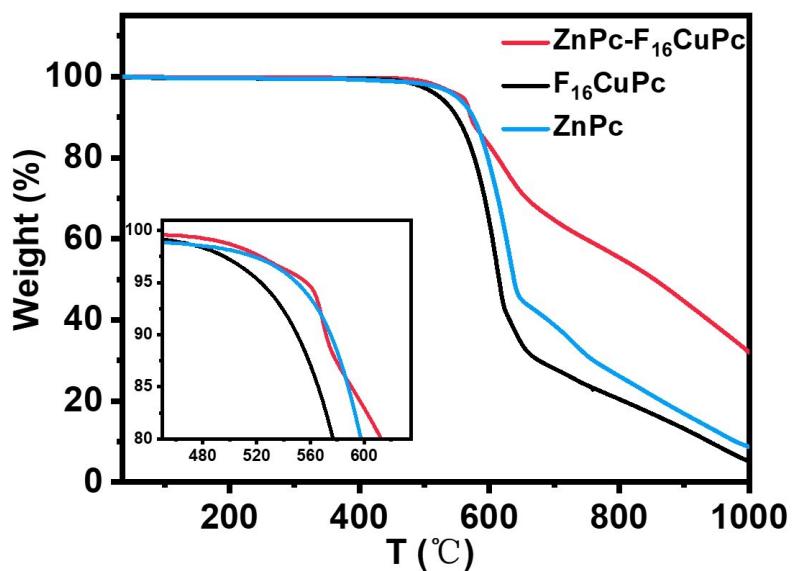


Fig. S2 TGA spectra of ZnPc, F₁₆CuPc and ZnPc–F₁₆CuPc.

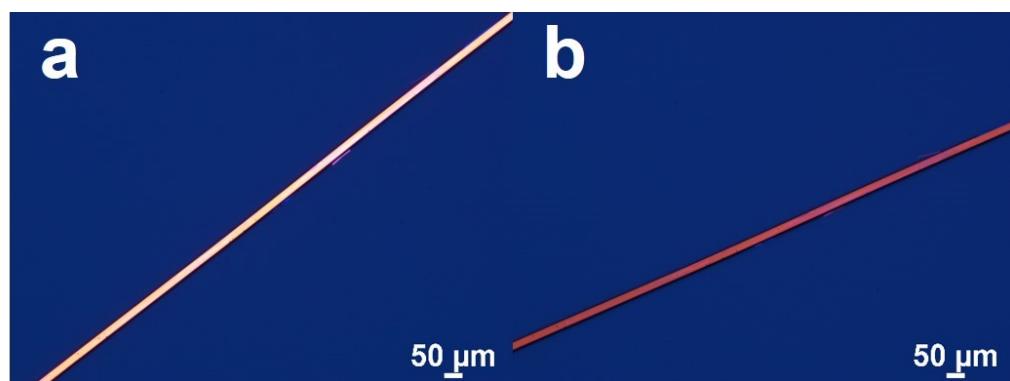


Fig. S3 Polarized optical microscope images of ZnPc–F₁₆CuPc cocrystal on the Si substrate with angles: (a) 0°, (b) 20°

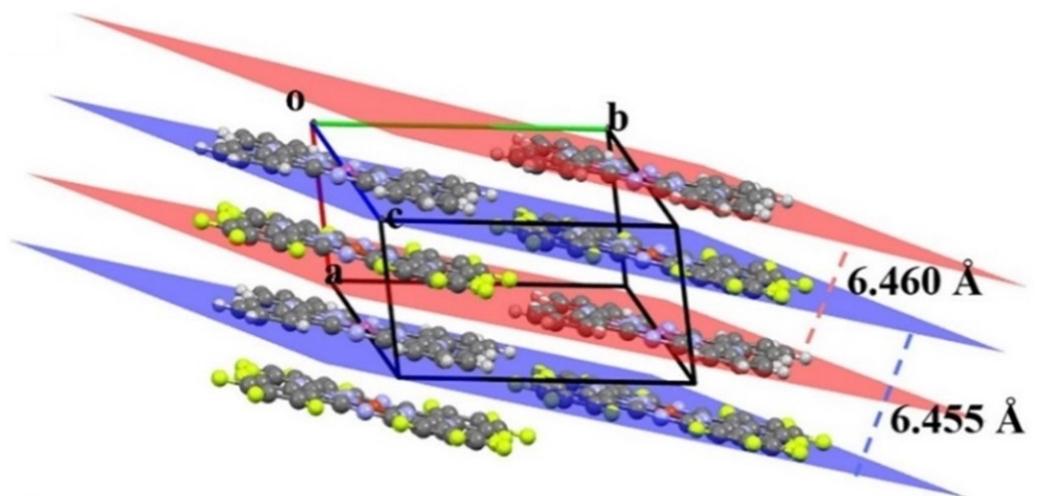


Fig. S4 The distance in ZnPc–F₁₆CuPc cocrystal.

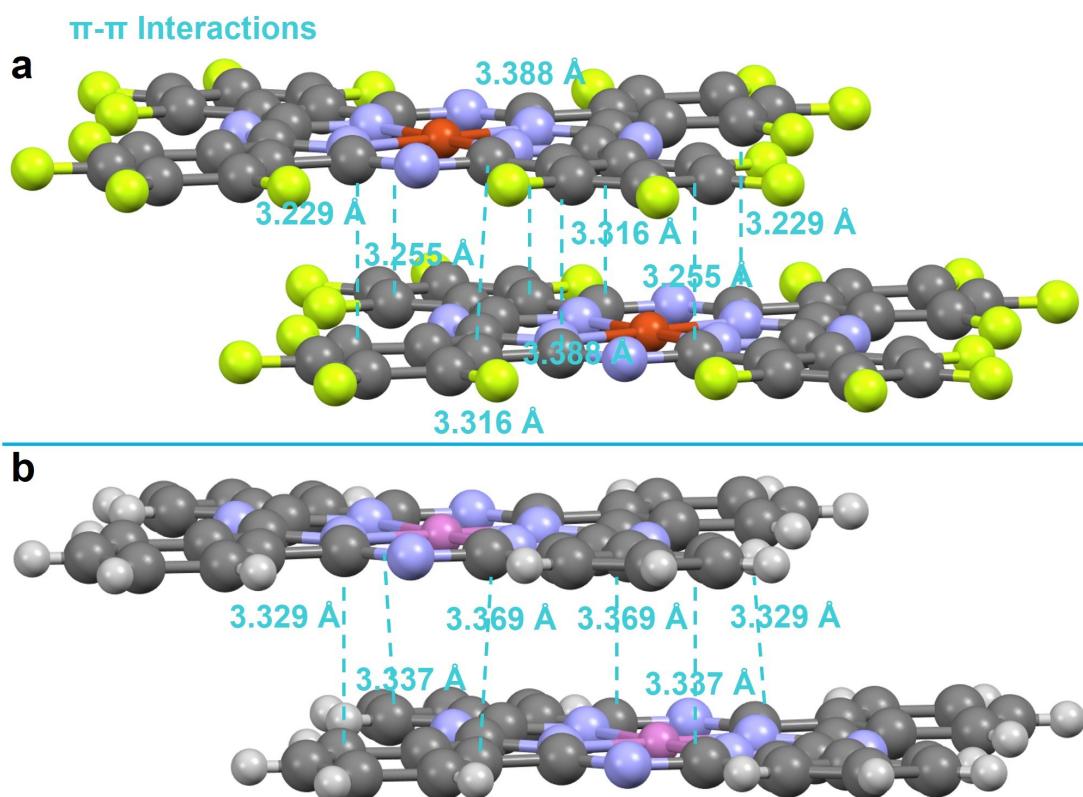


Fig. S5 The π-π interactions in (a) F₁₆CuPc and (b) ZnPc.



Fig. S6 Photo images of the typical bending configurations of a ZnPc–F₁₆CuPc needlelike cocrystal.

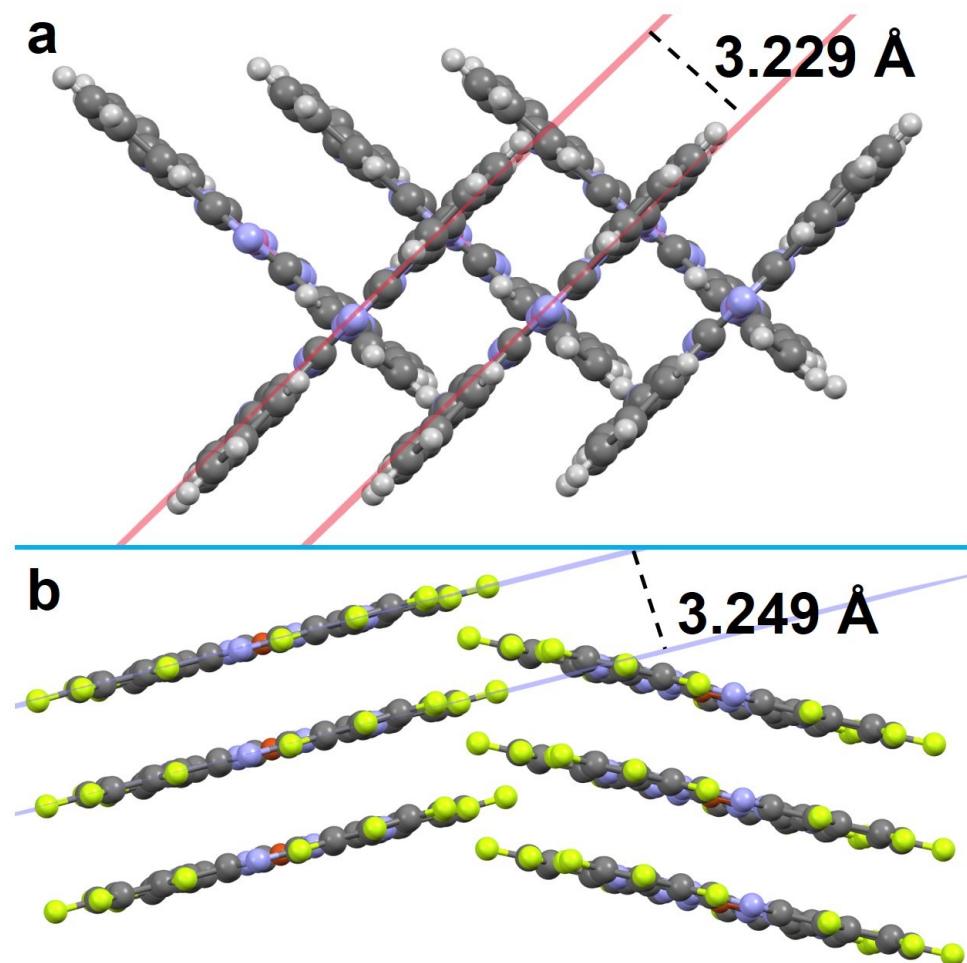


Fig. S7 The distance between (a) ZnPc molecules in ZnPc single crystal and (b) $F_{16}CuPc$ molecules in $F_{16}CuPc$ single crystal.

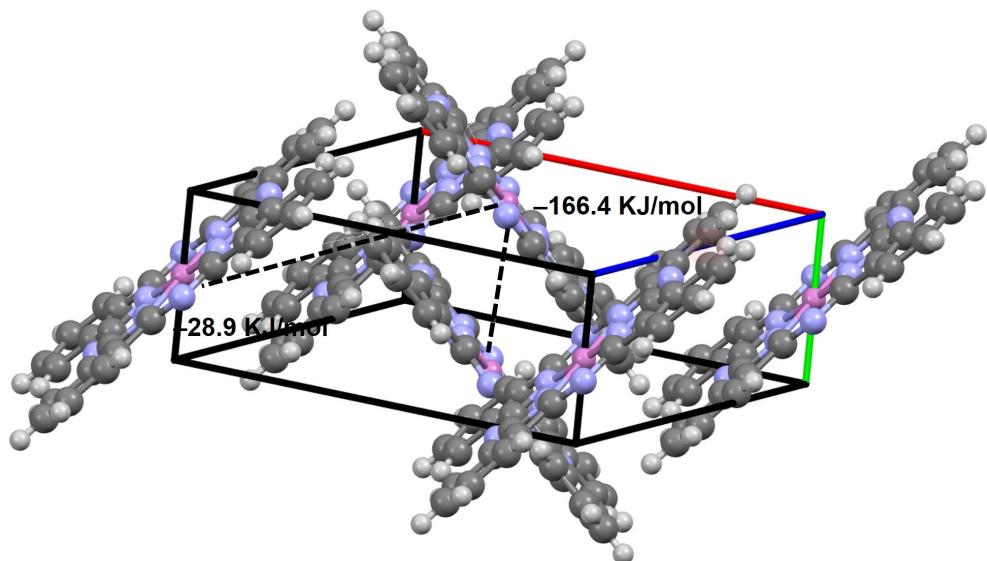


Fig. S8 The intermolecular potential energy of ZnPc.

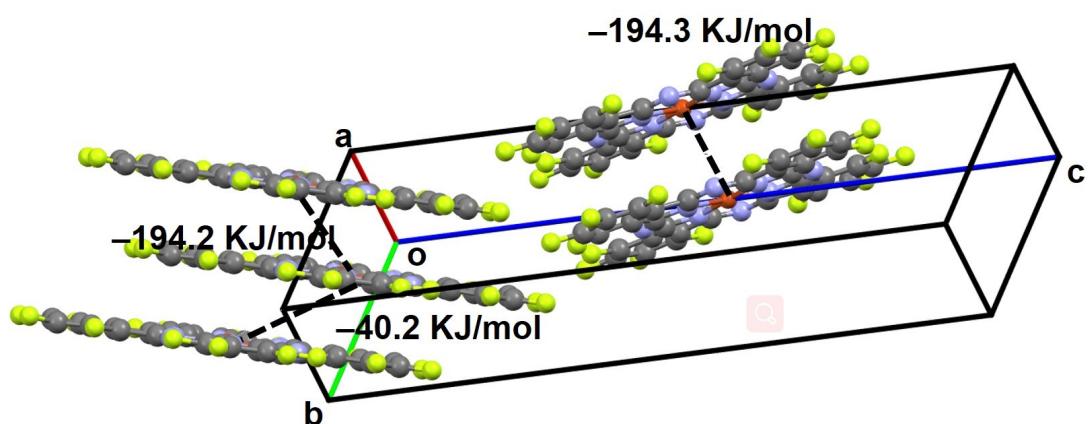


Fig. S9 The intermolecular potential energy of F_{16}CuPc .

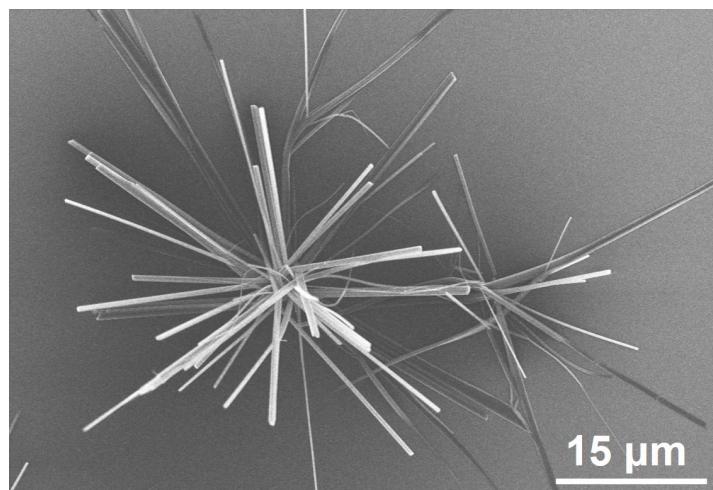


Fig. S10 The SEM image of $\text{ZnPc}-\text{F}_{16}\text{CuPc}$ nanobelts in-situ growing onto the Si/SiO_2 substrates.

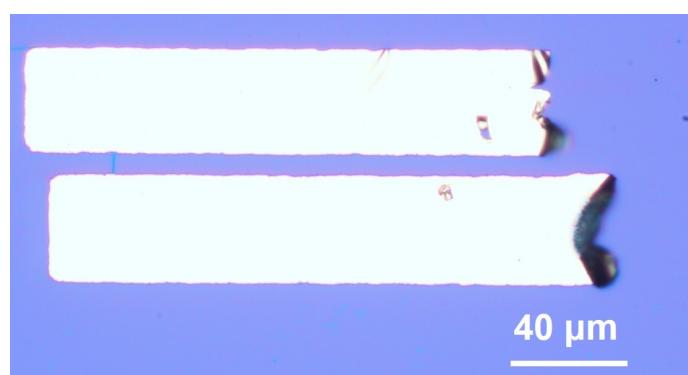


Fig. S11 Optical microscopy image of $\text{ZnPc}-\text{F}_{16}\text{CuPc}$ nanobelt FET.

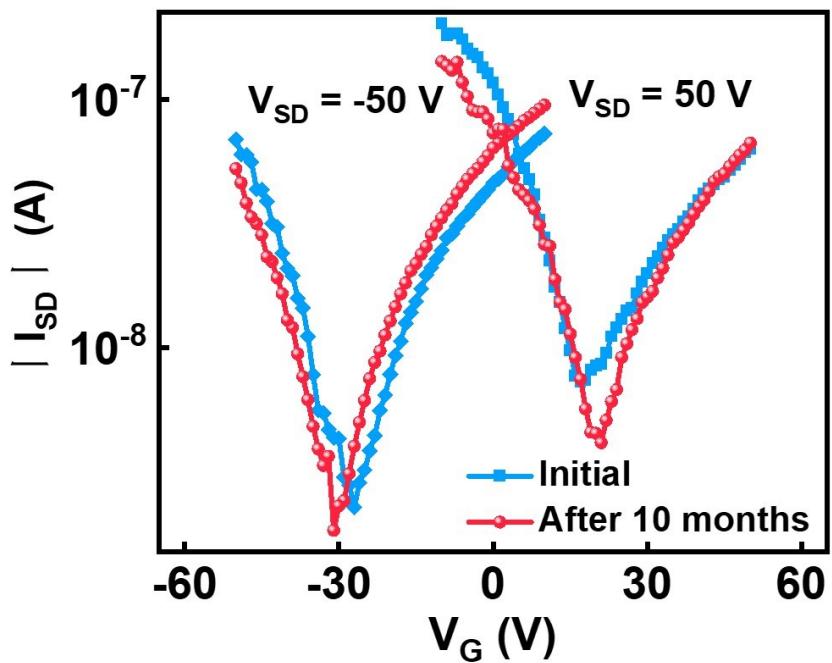


Fig. S12 The stability of the ZnPc–F₁₆CuPc cocrystal OFET after ten months of storage in air.

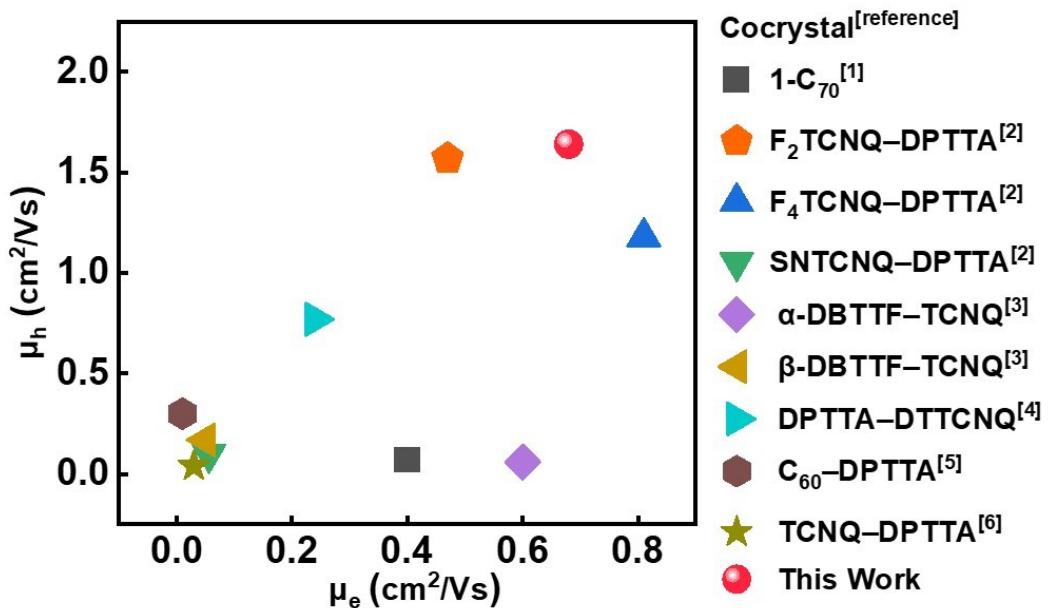


Fig. S13 Comparison of mobility based on ambipolar cocrystals with high-performance transport property for electron and hole in air.

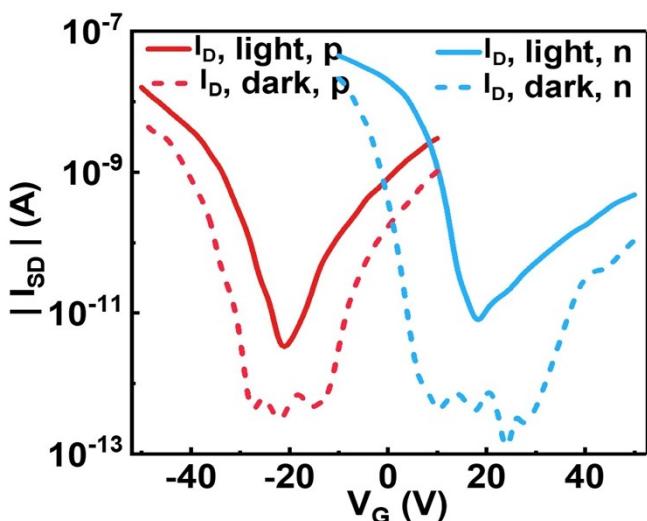


Fig. S14 The saturated transfer curves of the ZnPc–F₁₆CuPc cocrystal phototransistor operated in n-and p-channel under dark condition and 900 nm excitation pulse (160 $\mu\text{W cm}^{-2}$ illumination intensity). The channel area (W×L) is 0.37 $\mu\text{m} \times 17.5 \mu\text{m}$.

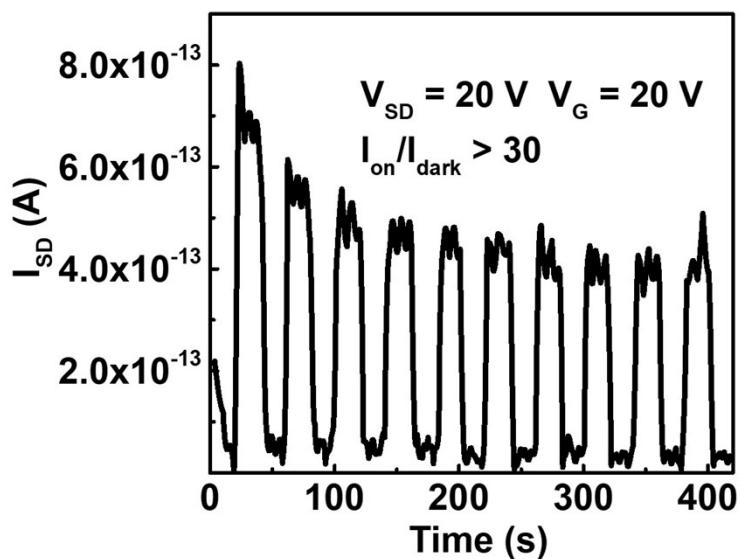


Fig. S15 Photoswitch of the cocrystal phototransistor under 900 nm excitation pulse (160 $\mu\text{W cm}^{-2}$ illumination intensity).

Table S1 Single crystal structure of ZnPc–F₁₆CuPc cocrystal.

Empirical formula	C ₆₄ H ₁₆ F ₁₆ N ₁₆ ZnCu	
Formula weight	1441.84	
Wavelength	1.54184 Å	
Crystal system	triclinic	
Space group	P -1	
Unit cell dimensions	$a=7.2654(2)$ Å $b=13.0351(3)$ Å $c=13.6626(3)$ Å $\alpha=85.043(2)^\circ$ $\beta=89.559(2)^\circ$ $\gamma=79.911(2)^\circ$	
Volume	1269.11 Å ³	
Z	1	
Density (calculated)	1.887 g cm ⁻³	
μ	2.23 mm ⁻¹	
F(000)	715	
Rint	0.0538	
Goof	1.182	
Final R indices [I>2sigma(I)]	R1=0.0708 wR2=0.2490	
R indices (all data)	R1=0.0740 wR2=0.2466	

Crystallographic data for the structure have been deposited with the Cambridge Crystallographic Data Centre (CCDC): ZnPc–F₁₆CuPc (CCDC: 2039946)

References

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